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(71) Applicant *(for all designated States except US)*: **LAM RESEARCH CORPORATION** [US/US]; 4650 Cushing Parkway, Fremont, CA 94538 (US).

(72) Inventors; and
(75) Inventors/Applicants *(for US only)*: **NGUYEN, Wendy** [US/US]; 3144 Rasmus Circle, San Jose, CA 95148 (US). **LEE, Chris** [US/US]; 6848 Aitken Drive, Oakland, CA 94611 (US).

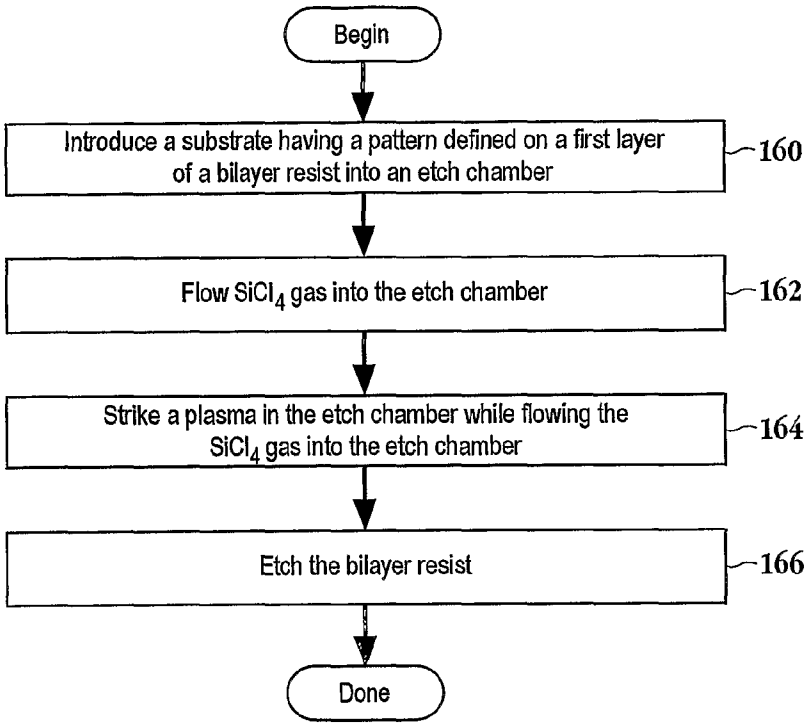
(74) Agent: **GENCARELLA, Michael, L.**; Martine Penilla & Gencarella, LLP, 710 Lakeway Drive, Suite 200, Sunnyvale, CA 94085 (US).

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[Continued on next page]

(54) Title: METHOD FOR BILAYER RESIST PLASMA ETCH



(57) Abstract: A method for etching a bilayer resist defined over a substrate in a plasma etch chamber is provided. The method initiates with introducing the substrate having a pattern defined on a first layer of the bilayer resist into the etch chamber. Then, $SiCl_4$ gas flows into the etch chamber. Next, a plasma is struck in the etch chamber while flowing the $SiCl_4$ gas. Then the bilayer resist is etched.

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